

Please replace the paragraph #0013 on application page 4 with the following paragraph:

-- An object of the invention is to provide an improved method for using a laser to create microfeatures in semiconductors, including silicon, gallium arsenide (GaAs), silicon carbide (SiC), silicon nitride (SiN), and/or Ge:Si, and/or also including such semiconductors subsequently treated in semiconductor processes, including but not limited to photolithography and etching, well known to those skilled in the art to contain additional layers for the purpose of creating useful electronic and optoelectronic circuits on semiconductor substrates, including semiconductor wafers. --

Please replace the paragraph #0043 on application page 9 with the following paragraph:

-- An optional laser power controller 52, such as a half wave plate polarizer, may be positioned along optical path 20. In addition, one or more beam detection devices 54, such as photodiodes, may be downstream of laser power controller 52, such as aligned with a positioning mirror 44 that is adapted to be partly transmissive to the wavelength of laser output 16. Beam detection devices 54 are preferably in communication with beam diagnostic electronics that convey signals to modify the effects of laser power controller 52. --